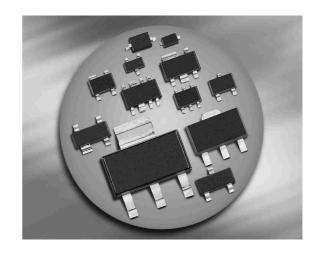


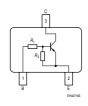
PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor (R_1 =2.2 k Ω , R_2 =47 k Ω)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101





BCR158 BCR158W



Туре	Marking	Pin Configuration					Package	
BCR158	WIs	1=B	2=E	3=C	-	-	-	SOT23
BCR158W	Wls	1=B	2=E	3=C	-	-	-	SOT323

Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	50	V	
Collector-base voltage	V_{CBO}	50		
Input forward voltage	$V_{i(fwd)}$	20		
Input reverse voltage	V _{i(rev)}	5		
Collector current	I _C	100	mA	
Total power dissipation-	P _{tot}		mW	
BCR158, <i>T</i> _S ≤ 102°C		200		
BCR158W, <i>T</i> _S ≤ 124°C		250		
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-65 150		

1



Thermal Resistan	nce
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Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR158		≤ 240	
BCR158W		≤ 105	

Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol		Values			
		min.	typ.	max.		
DC Characteristics			1	r		
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	50	-	-	V	
$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm B} = 0$						
Collector-base breakdown voltage	$V_{(BR)CBO}$	50	-	-		
$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$						
Collector-base cutoff current	I _{CBO}	-	-	100	nA	
$V_{\rm CB} = 40 \text{ V}, I_{\rm E} = 0$						
Emitter-base cutoff current	I _{EBO}	-	-	164	μΑ	
$V_{\rm EB} = 5 \text{V}, I_{\rm C} = 0$						
DC current gain ²⁾	h _{FE}	70	-	-	-	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 5 V						
Collector-emitter saturation voltage ²⁾	V _{CEsat}	-	-	0.3	V	
$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0.5 mA						
Input off voltage	$V_{\rm i(off)}$	0.4	_	0.8		
$I_{\rm C}$ = 100 μ A, $V_{\rm CE}$ = 5 V						
Input on voltage	$V_{i(on)}$	0.5	-	1.1		
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V						
Input resistor	R_1	1.5	2.2	2.9	kΩ	
Resistor ratio	R_1/R_2	0.042	0.047	0.052	_	
AC Characteristics						
Transition frequency	f _T	-	200	-	MHz	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5 V, f = 100 MHz						
Collector-base capacitance	C _{cb}	-	3	-	pF	
$V_{\rm CB} = 10 \text{ V}, f = 1 \text{ MHz}$						

 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

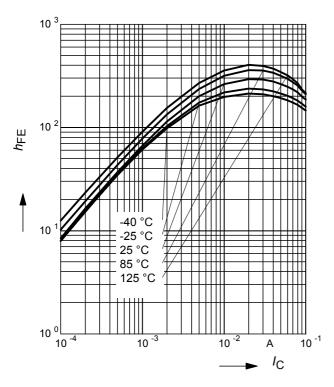
2

 $^{^2}$ Pulse test: t < 300 μ s; D < 2%



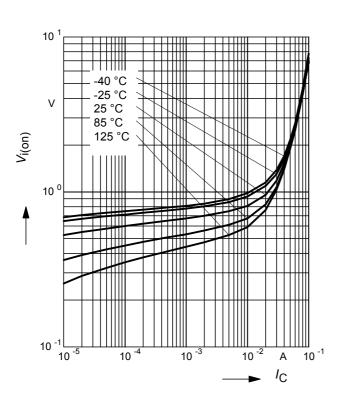
DC current gain $h_{FE} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)



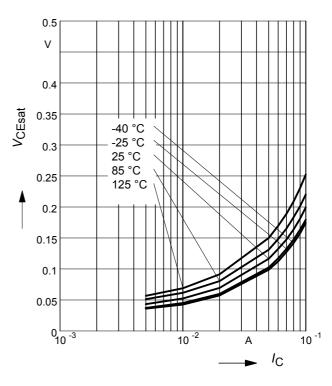
Input on Voltage $Vi_{(On)} = f(I_C)$

 V_{CE} = 0.3V (common emitter configuration)



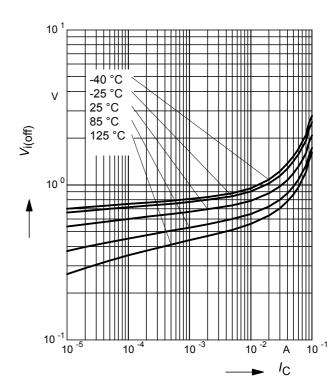
Collector-emitter saturation voltage

 $V_{CEsat} = f(I_{C}), I_{C}/I_{B} = 20$



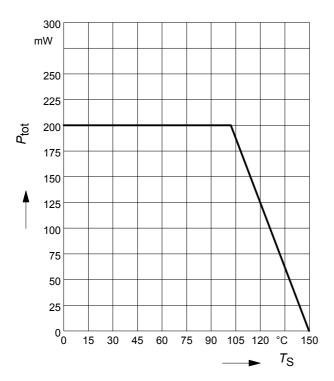
Input off voltage $V_{i(Off)} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)

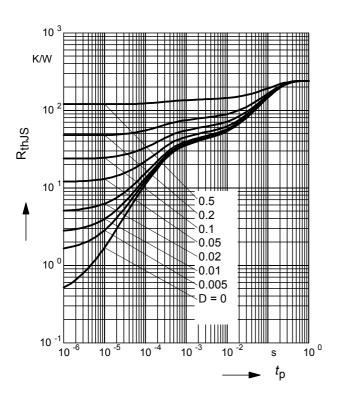




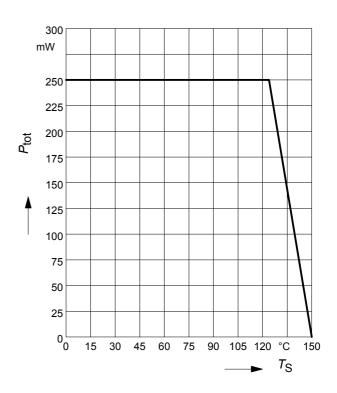
Total power dissipation $P_{tot} = f(T_S)$ BCR158



Permissible Pulse Load $R_{thJS} = f(t_p)$ BCR158

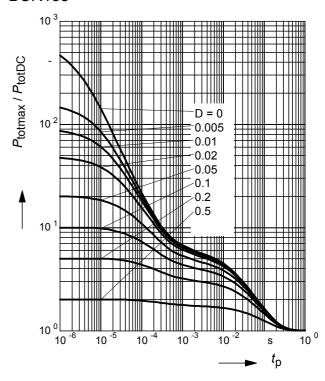


Total power dissipation $P_{tot} = f(T_S)$ BCR158W



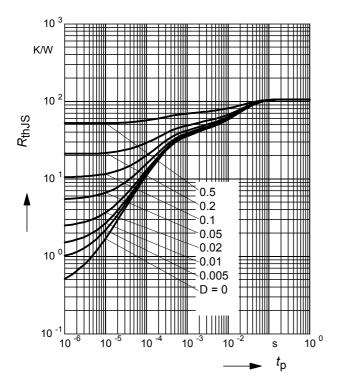
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$ BCR158



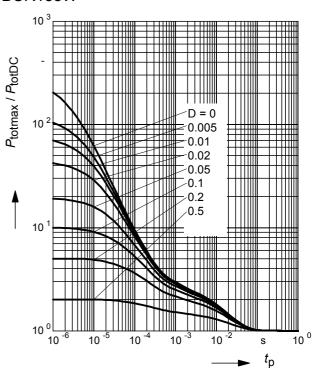


Permissible Puls Load $R_{thJS} = f(t_p)$ BCR158W



Permissible Pulse Load

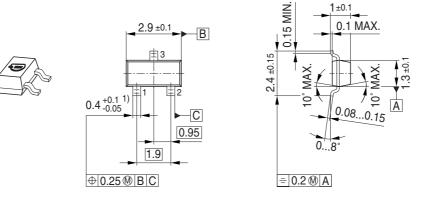
 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$ BCR158W



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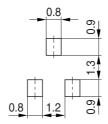


Package Outline

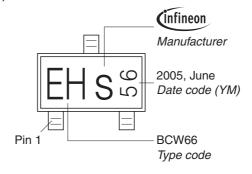


1) Lead width can be 0.6 max. in dambar area

Foot Print

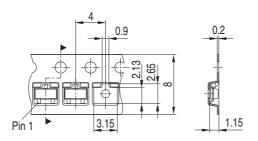


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

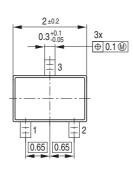


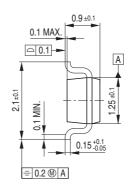
6



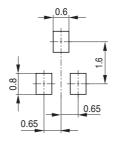
Package Outline



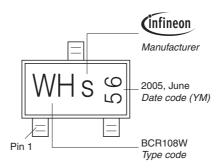




Foot Print

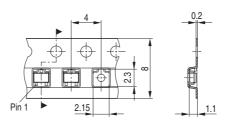


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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